Hex Inverter

With LSTTL-Compatible Inputs High-Performance Silicon-Gate CMOS

The 74HCT04 may be used as a level converter for interfacing TTL or NMOS outputs to High-Speed CMOS inputs. The HCT04A is identical in pinout to the LS04.

Features

- Output Drive Capability: 10 LSTTL Loads
- TTL/NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance With the JEDEC Standard No. 7A Requirements
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 48 FETs or 12 Equivalent Gates
- These are Pb-Free Devices



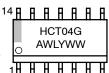
ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



HCT04 = Device Code

A = Assembly Location

L, WL = Wafer Lot Y = Year

W, WW = Work Week

G or ■ = Pb-Free Package

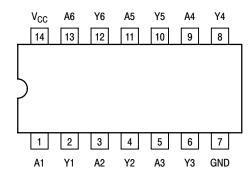
ORDERING INFORMATION

(Note: Microdot may be in either location)

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

1

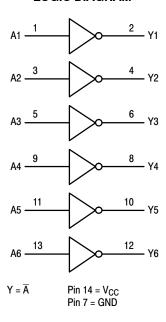
Pinout: 14-Lead Packages (Top View)



FUNCTION TABLE

Inputs	Outputs	
Α	Y	
L	н	
Н	L	

LOGIC DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping [†]
74HCT04DR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
74HCT04DTR2G	TSSOP-14*	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb-Free.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	$-$ 0.5 to V_{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	±20	mA
l _{out}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±50	mA
P _D	Power Dissipation in Still Air SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature Range	- 65 to + 150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature Range, All Package Types	– 55	+ 125	°C
t _r , t _f	Input Rise/Fall Time (Figure 1)	0	500	ns

DC CHARACTERISTICS (Voltages Referenced to GND)

				V _{CC}	Guaranteed Limit			
Symbol	Parameter	Condi	tion	(V)	-55 to 25°C	≤ 85 °C	≤125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1V$ $ I_{out} \le 20\mu A$		4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V_{IL}	Maximum Low-Level Input Voltage	$V_{out} = V_{CC} - 0.1$ $ I_{out} \le 20\mu A$	/	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out} \le 20\mu A$		4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		V _{in} = V _{IL}	$ I_{out} \le 4.0 \text{mA}$	4.5	3.98	3.84	3.70	
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20\mu A$		4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	٧
		V _{in} = V _{IH}	$ I_{out} \le 4.0 \text{mA}$	4.5	0.26	0.33	0.40	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GNI)	5.5	±0.1	±1.0	±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GNI $I_{out} = 0\mu A$)	5.5	2.0	20	40	μΑ
ΔI_{CC}	Additional Quiescent Supply Current	V _{in} = 2.4V, Any C V _{in} = V _{CC} or GNI	•		≥ -55°C	25 to	125°C	
	Ounent	$I_{out} = 0 \mu A$, Other Inputs	5.5	2.9	2	.4	mA

^{1.} Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

^{2.} Total Supply Current = $I_{CC} + \Sigma \Delta I_{CC}$.

AC CHARACTERISTICS (V_{CC} = 5.0V ±10%, C_L = 50pF, Input t_r = t_f = 6ns)

		Guaranteed Limit			
Symbol	Parameter	-55 to 25°C	≤85°C	≤125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 2)	15 17	19 21	22 26	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 2)	15	19	22	ns
C _{in}	Maximum Input Capacitance	10	10	10	pF

^{3.} For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Inverter)*	22	pF

^{*} Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

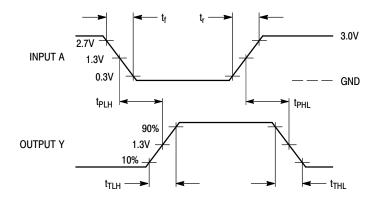
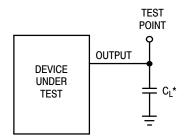


Figure 1. Switching Waveforms



*Includes all probe and jig capacitance

Figure 2. Test Circuit

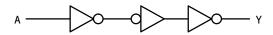
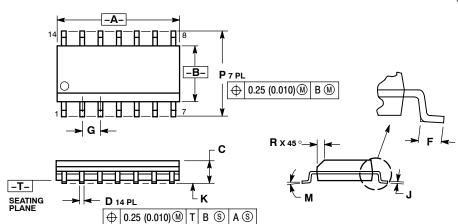


Figure 3. Expanded Logic Diagram (1/6 of the Device Shown)

PACKAGE DIMENSIONS

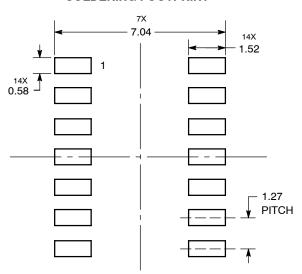
SOIC-14 CASE 751A-03 **ISSUE H**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7 °	0 °	7 °
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT*

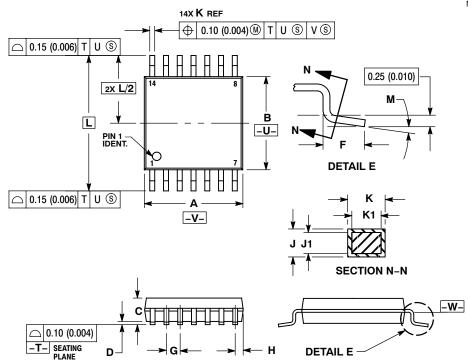


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-14 CASE 948G-01 **ISSUE B**



NOTES:

- OTES:

 1. DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD
 FLASH, PROTRUSIONS OR GATE BURRS.
 MOLD FLASH OR GATE BURRS SHALL NOT
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

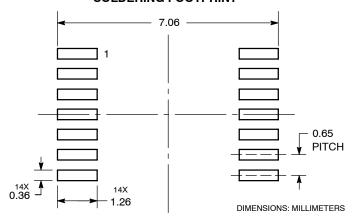
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR
- 6. TERMINAL NUMBERS ARE SHOWN FOR
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
М	0 °	8°	0°	8 °	

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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